

TP65H030G4PWS

650V SuperGaN® GaN FET in TO-247-3 (source tab)

Description

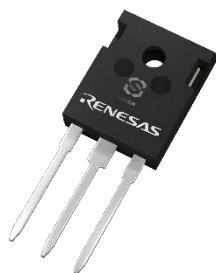
The TP65H030G4PWS 650V, 30mΩ Gallium Nitride (GaN) FET is a normally-off device using Renesas' Gen IV plus platform. It combines a state-of-the-art high voltage GaN HEMT with a low voltage silicon MOSFET to offer superior performance, standard drive, ease of adoption and reliability.

The Gen IV plus SuperGaN® platform uses advanced epi and patented design technologies to simplify manufacturability while improving efficiency over silicon via lower gate charge, output capacitance, crossover loss, and reverse recovery charge.

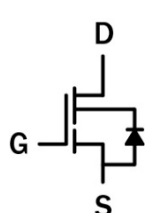
Benefits

- Superior normally off architecture with D-mode GaN HEMT
- Compatible with standard silicon drivers
- Enhanced noise immunity with a 4V threshold voltage with no negative gate drive required
- Enables high-efficiency, high power density, and reliable power conversion
- Facilitates cost-effective GaN adoption reducing system size, weight, and costs

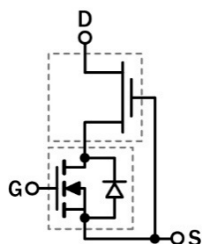
Product/Schematic Diagrams



TP65H030G4PWS TO-247-3



Cascode Schematic Symbol



Cascode Device Structure

Features

- Ultra-fast switching Gen IV plus GaN
- JEDEC-qualified GaN technology
- Dynamic $R_{DS(on)eff}$ production tested
- Reduced crossover loss
- Negligible Q_{rr}
- RoHS compliant and Halogen-free packaging

Applications

- AI datacenter and telecom power supplies
- E-mobility charging
- PV inverter
- UPS
- BESS



Specifications

V_{DS} (V)	650
$V_{DSS(TR)}$ (V) maximum	800
$R_{DS(on)}$ (mΩ) maximum ^[1]	37
Q_{OSS} (nC) typical	135
Q_G (nC) typical	24.5

1. Dynamic $R_{DS(on)}$ (see Figure 17 and Figure 18)

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1. Pin Information

1.1 Pin Assignments Source.

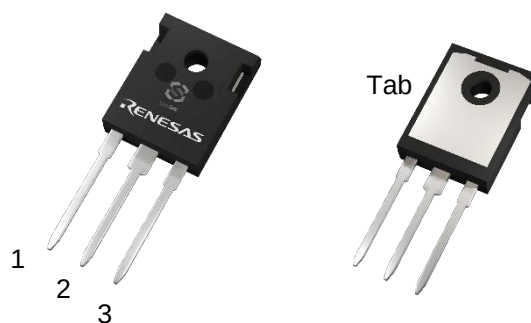


Figure 1. Pin Assignments – Bottom View

1.2 Pin Descriptions

Pin Number	Pin Name	Description
1	G	Gate.
2	S	Source.
3	D	Drain.
Tab	S	Source.

2. Specifications

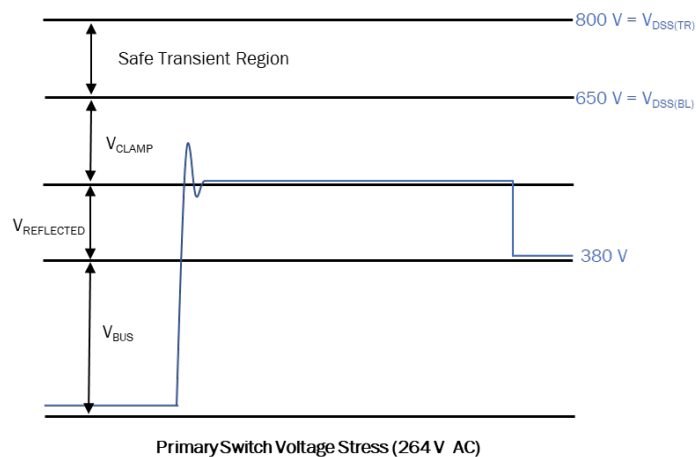
2.1 Absolute Maximum Ratings

$T_c = 25^\circ\text{C}$ unless otherwise stated.

Caution: Do not operate at or near the maximum ratings listed for extended periods of time. Exposure to such conditions can adversely impact product reliability and result in failures not covered by warranty.

Symbol	Parameter	Minimum	Maximum	Unit
V_{DSS}	Drain to source voltage ($T_J = -55^\circ\text{C}$ to 150°C)	-	650	V
$V_{DSS(TR)}$	Transient drain to source voltage ^[1]	-	800	
$V_{DSS(TR)}, \text{ pulsed}$	Drain to source voltage, pulsed ^[2]	-	750	
V_{GSS}	Gate to source voltage	-20	+20	
P_D	Maximum power dissipation at $T_c = 25^\circ\text{C}$	-	192	W
I_D	Continuous drain current at $T_c = 25^\circ\text{C}$	-	55.7	A
	Continuous drain current at $T_c = 100^\circ\text{C}$	-	35	A
I_{DM}	Pulsed drain current (pulse width: 10 μs)	-	230	A
T_J	Operating temperature junction	-55	+150	$^\circ\text{C}$
T_S	Storage temperature	-55	+150	$^\circ\text{C}$
T_{SOLD}	Soldering peak temperature ^[3]	-	260	$^\circ\text{C}$

- $V_{GS} = 0\text{V}$, $\leq 10\mu\text{s}$, $\leq 1\%$ Duty Cycle, cumulative 60s (60 million pulses).
- $V_{GS} = 0\text{V}$, $\leq 1\mu\text{s}$, $\leq 1\%$ Duty Cycle, cumulative 10h (36 billion pulses).
- For 10 sec., 1.6mm from the case.



2.2 Thermal Specifications

Symbol	Condition	Typical Value	Unit
$R_{\theta JC}$	Junction-to-case	0.65	$^\circ\text{C/W}$
$R_{\theta JA}$	Junction-to-ambient	40	

2.3 Electrical Specifications – Forward Device

$T_J = 25^\circ\text{C}$ unless otherwise stated.

Symbol	Parameter	Test Conditions	Minimum	Typical	Maximum	Unit
$V_{DSS(BL)}$	Maximum drain-source voltage	$V_{GS} = 0V$	650	-	-	V
$V_{GS(th)}$	Gate threshold voltage	$V_{DS} = V_{GS}, I_D = 1mA$	3.3	4	4.8	V
$\Delta V_{GS(th)}/T_J$	Gate threshold voltage temperature coefficient		-	-6.5	-	mV/ $^\circ\text{C}$
$R_{DS(on)eff}$	Drain-source on-resistance ^[1]	$V_{GS} = 12V, I_D = 30A, T_J = 25^\circ\text{C}$	-	30	37	m Ω
		$V_{GS} = 12V, I_D = 30A, T_J = 150^\circ\text{C}$	-	62	-	
I_{DSS}	Drain-to-source leakage current	$V_{DS} = 650V, V_{GS} = 0V, T_J = 25^\circ\text{C}$	-	3	30	μA
		$V_{DS} = 650V, V_{GS} = 0V, T_J = 150^\circ\text{C}$	-	20	-	
I_{GSS}	Gate-to-source forward leakage current	$V_{GS} = 20V$	-	-	400	nA
	Gate-to-source reverse leakage current	$V_{GS} = -20V$	-	-	-400	
C_{iss}	Input capacitance	$V_{GS} = 0V, V_{DS} = 400V, f = 1MHz$	-	1500	-	pF
C_{oss}	Output capacitance		-	127	-	
C_{rss}	Reverse transfer capacitance		-	4.6	-	
$C_{O(er)}$	Output capacitance, energy related ^[2]	$V_{GS} = 0V, V_{DS} = 0V \text{ to } 400V$	-	183	-	pF
$C_{O(tr)}$	Output capacitance, time related ^[3]		-	339	-	
Q_G	Total gate charge	$V_{DS} = 400V, V_{GS} = 0V \text{ to } 12V, I_D = 30A$	-	24.5	-	nC
Q_{GS}	Gate-source charge		-	8.4	-	
Q_{GD}	Gate-drain charge		-	6.6	-	
Q_{oss}	Output charge	$V_{GS} = 0V, V_{DS} = 0V \text{ to } 400V$	-	135	-	nC
$t_{D(on)}$	Turn-on delay	$V_{DS} = 400V, V_{GS} = 0V \text{ to } 12V, R_{G(on)} = 10\Omega, R_{G(off)} = 30\Omega, I_D = 30A, Z_{FB} = 180\Omega \text{ at } 100MHz \text{ (see Figure 15)}$	-	40.8	-	ns
t_R	Rise time		-	6.8	-	
$t_{D(off)}$	Turn-off delay		-	89.2	-	
t_F	Fall time		-	8	-	

1. Dynamic $R_{DS(on)}$, 100% tested; see [Figure 17](#) and [Figure 18](#) for conditions.
2. Equivalent capacitance to give same stored energy from 0V to 400V.
3. Equivalent capacitance to give same charging time from 0V to 400V.

2.4 Electrical Specifications – Reverse Device

$T_J = 25^\circ\text{C}$ unless otherwise stated.

Symbol	Parameter	Test Conditions	Minimum	Typical	Maximum	Unit
I_S	Reverse current	$V_{GS} = 0V$, $T_C = 100^\circ\text{C}$, $\leq 25\%$ duty cycle	-	-	32	A
V_{SD}	Reverse voltage ^[1]	$V_{GS} = 0V$, $I_S = 32A$	-	1.8	-	V
		$V_{GS} = 0V$, $I_S = 16A$	-	1.3	-	

1. Includes dynamic $R_{DS(on)}$ effect.

Note: Reverse recovery charge is negligible, enabled by the LV Si FET technology

3. Typical Performance Graphs

$T_c = 25^\circ\text{C}$ unless otherwise stated.

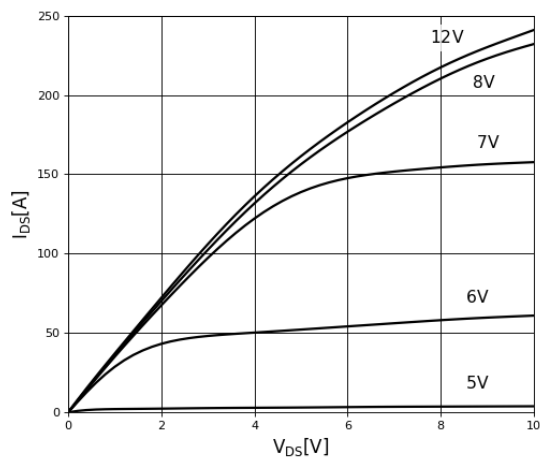


Figure 2. Typical Output Characteristics, $T_J = 25^\circ\text{C}$

Parameter: V_{GS}

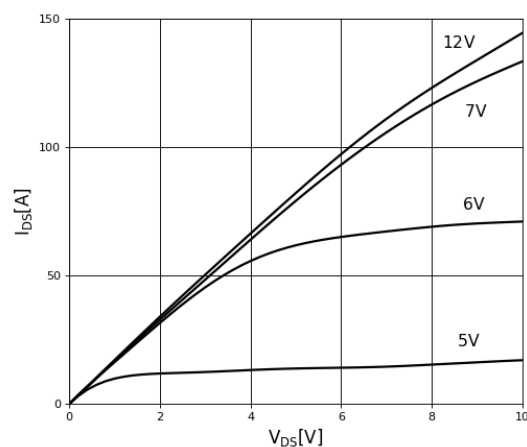


Figure 3. Typical Output Characteristics, $T_J = 150^\circ\text{C}$

Parameter: V_{GS}

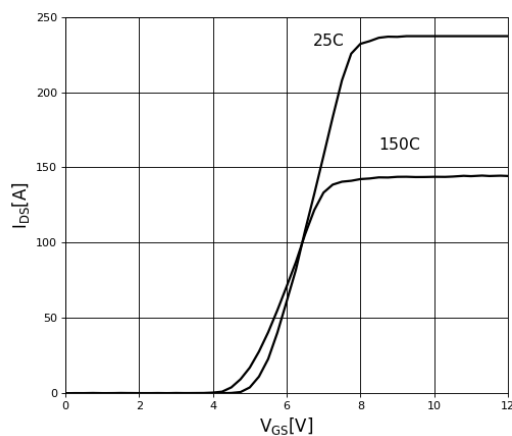


Figure 4. Typical Transfer Characteristics

$V_{DS} = 10\text{V}$, Parameter: T_J

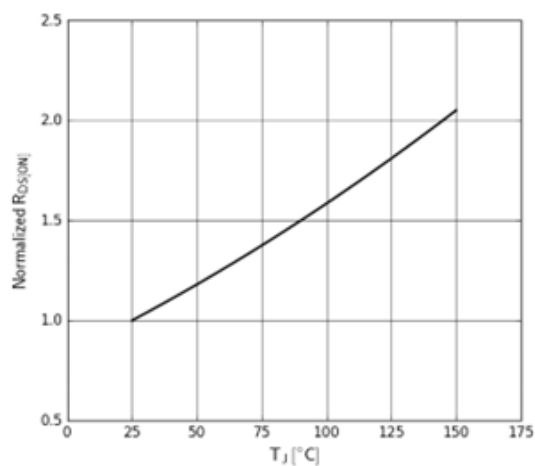


Figure 5. Normalized On-resistance

$I_D = 30\text{A}$, $V_{GS} = 12\text{V}$

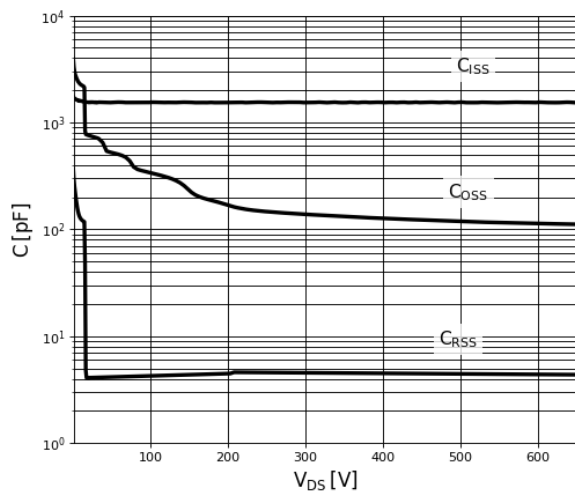


Figure 6. Typical Capacitance

$V_{GS} = 0\text{V}$, $f = 1\text{MHz}$

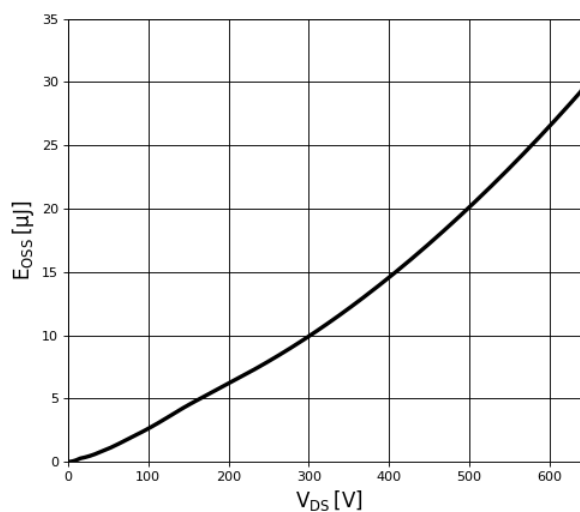


Figure 7. Typical C_{OSS} Stored Energy

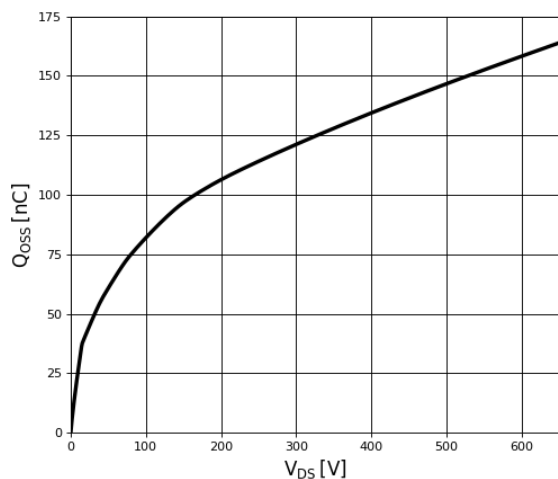


Figure 8. Typical Q_{oss}

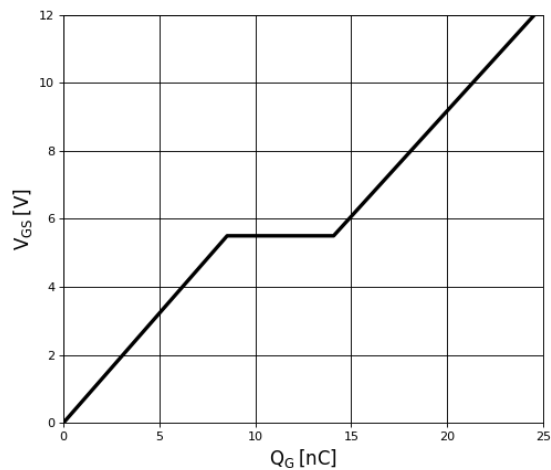


Figure 9. Typical Gate Charge

$I_{DS} = 30A$, $V_{DS} = 400V$

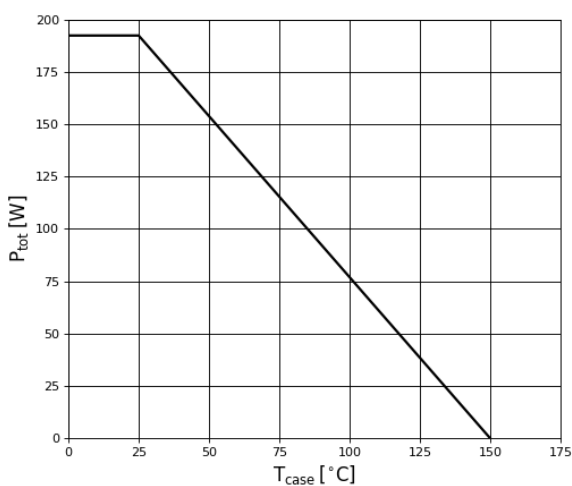


Figure 10. Power Dissipation

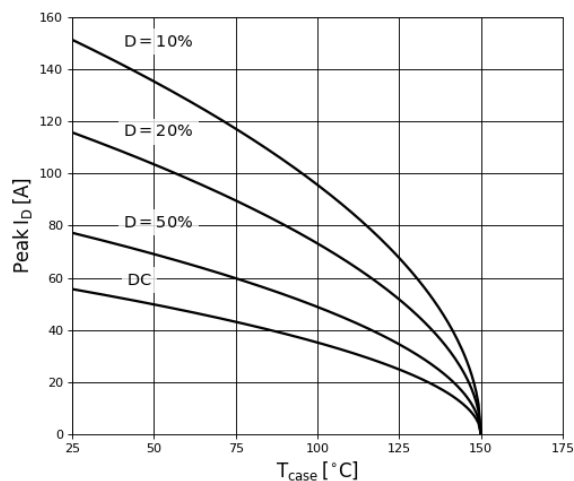


Figure 11. Current Derating

Pulse width $\leq 10\mu s$, $V_{GS} \geq 12V$

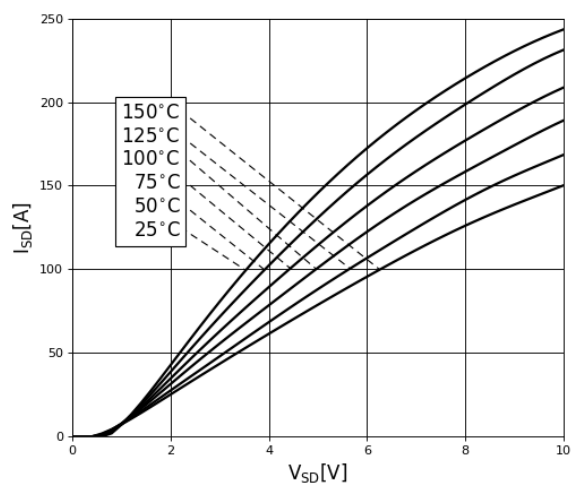


Figure 12. Forward Characteristics of Rev. Diode

$I_S = f(V_{SD})$, Parameter: T_J

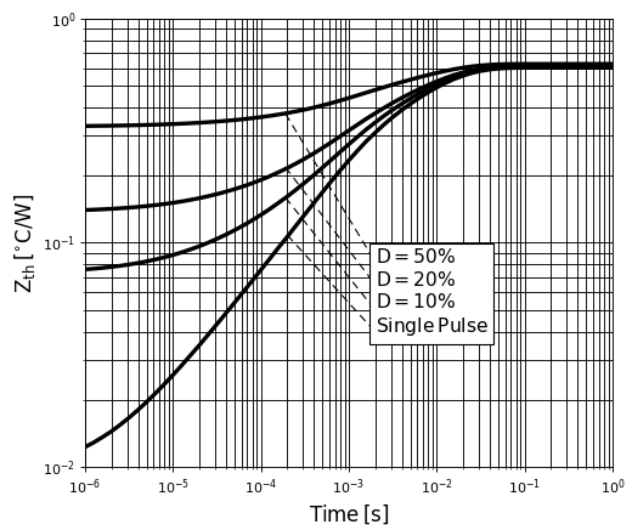


Figure 13. Transient Thermal Resistance

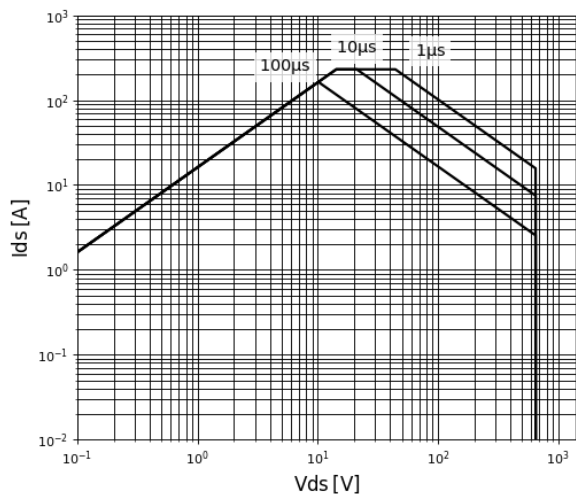


Figure 14. Safe Operating Area $T_C = 25^\circ\text{C}$

4. Test Circuits and Waveforms

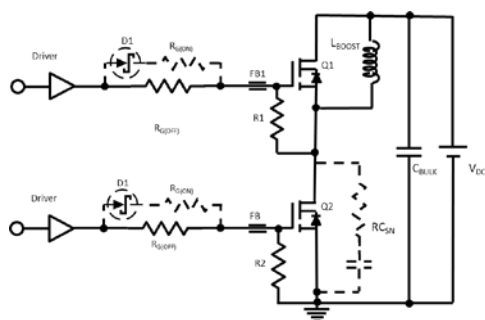


Figure 15. Switching Time Test Circuit

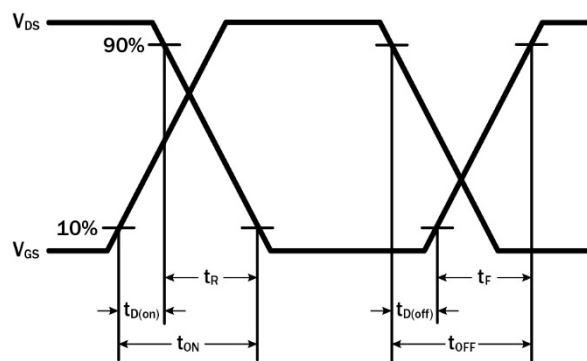


Figure 16. Switching Time Waveform

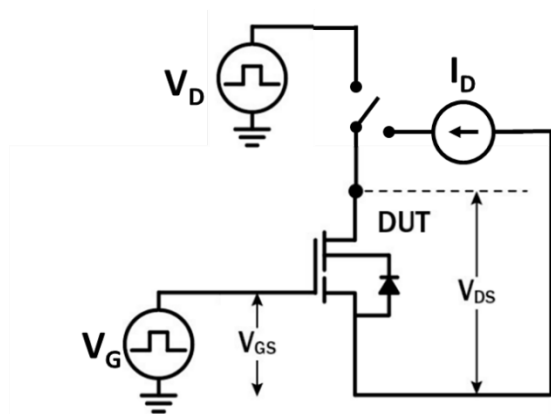


Figure 17. Dynamic $R_{DS(on)eff}$ Test Circuit

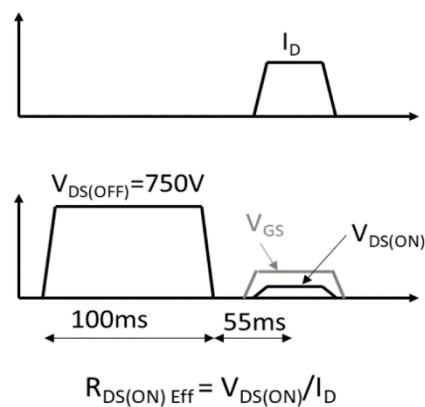


Figure 18. Dynamic $R_{DS(on)eff}$ Waveform

5. Package Outline Drawings

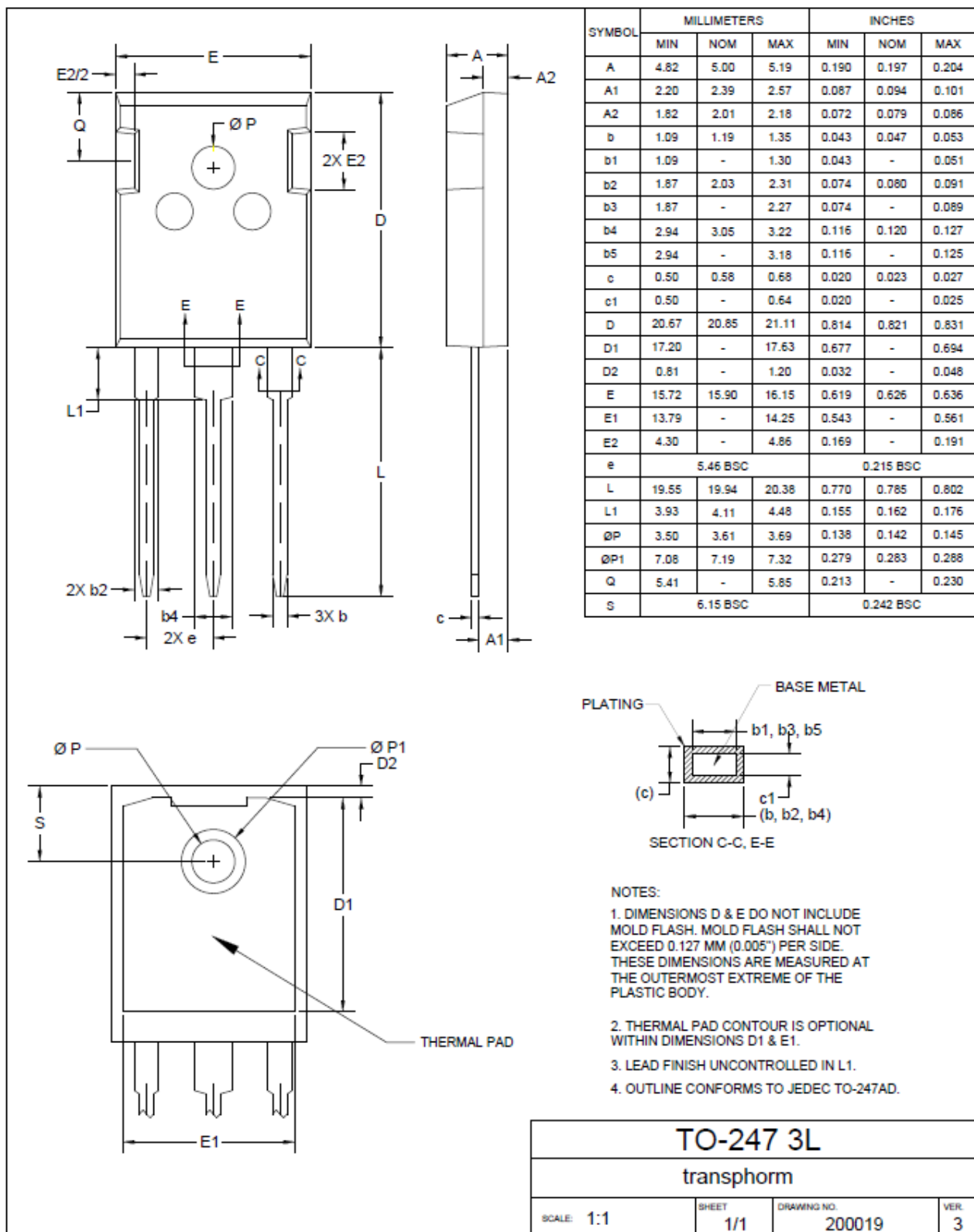


Figure 19. TO-247 3L Package Outline Drawing

6. Related Information

All technical documents for Renesas GaN Power devices are accessible from the [GaN Power Solutions](#) page.

7. Ordering Information

Part Number	Package Description	Package Configuration
TP65H030G4PWS	TO-247 3L	Source

8. Revision History

Revision	Date	Description
2.01	Jun 29, 2026	Updated maximum Rds(on) specification.
2.00	Nov 25, 2025	Updated the document's formatting; no technical changes were completed.
1.00	May 13, 2025	Initial release.